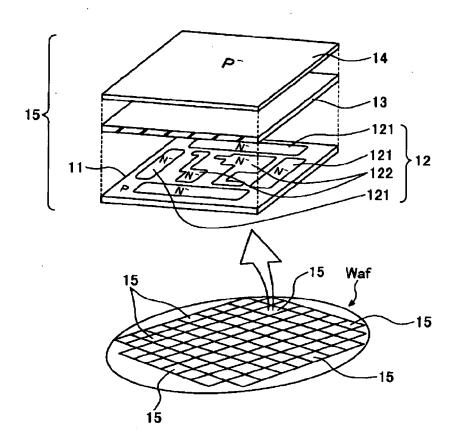
FIG.1



2/7

FIG.2

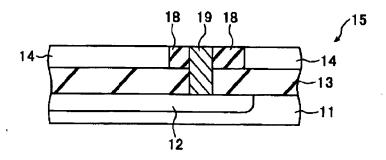


FIG.3 (a)

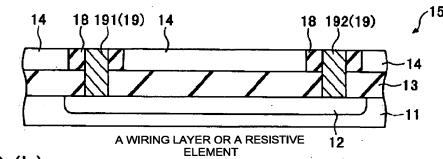


FIG.3 (b) 14 (MAKING THE LAYER LOW RESISTIVITY) 19 18 141 12

**ACAPACITIVE ELEMENT** 

FIG.4 (a)



FIG.4 (b)

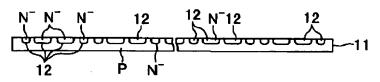


FIG.4 (c)

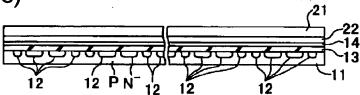
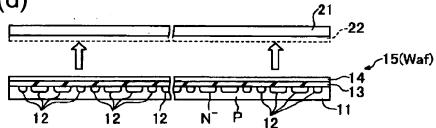


FIG.4 (d)



Title: SEMICONDUCTOR SUBSTRATE HAVING SOI STRUCTURE AND MANUFACTURING METHOD AND SEMICONDUCTOR DEVICE THEREOF

Inventor: Kazuo TAGUCHI Atty. Ref.: 9319S-000578

FIG.5

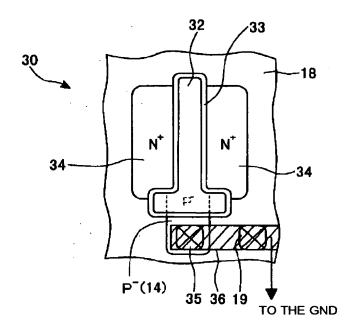


FIG.6

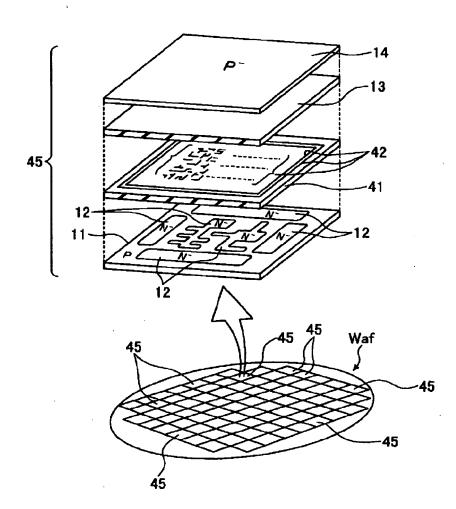


FIG.7

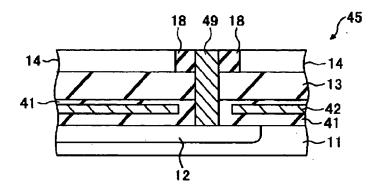


FIG.8

